

60V N-Channel Power MOSFET

DESCRIPTION

The IRF3205S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

Application

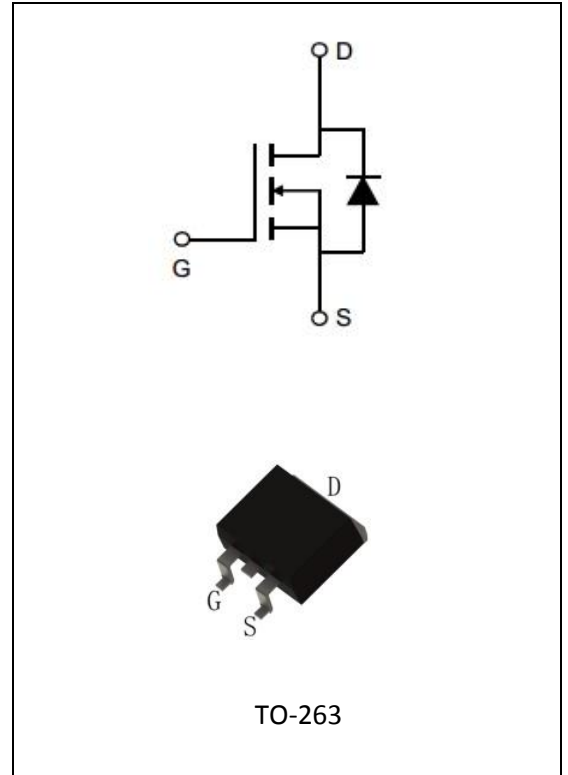
- ① Power switching application
- ② Hard switched and High frequency circuits
- ③ Uninterruptible power supply

KEY CHARACTERISTICS

- ① $V_{DS} = 60V, I_D = 120A$
- ② $R_{DS(ON)} < 7m\Omega @ V_{GS}=10V$
- ③ Special process technology for high ESD capability
- ④ High density cell design for lower R_{dson}
- ⑤ Fully characterized avalanche voltage and current
- ⑥ Good stability and uniformity with high EAS
- ⑦ Excellent package for good heat dissipation

100% UIS TESTED !

100% DVDS TESTED !



Package Marking And Ordering Information

Ordering Codes	Package	Product Code	Packing
IRF3205S	TO-263	IRF3205S	Reel

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	120	A
Drain Current-Pulsed (Note 1)	I_{DM}	380	A
Maximum Power Dissipation($T_c=25^\circ C$)	P_D	143	W
Single pulse avalanche energy(Note 2)	EAS	260	mJ
Operating Junction and Storage Temperature Range	$T_J, T_s T_g$	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	1.05	$^{\circ}\text{C}/\text{W}$
Thermal Resistance,Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics (TA=25 $^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu\text{A}$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2	2.8	4	V
Drain-Source On-State Resistance ^(Note 3)	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$	-	6.0	7.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=15A$	-	15	-	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	3700	-	pF
Output Capacitance	C_{oss}		-	345	-	pF
Reverse Transfer Capacitance	C_{rss}		-	270	-	pF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=30A,$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	19	-	nS
Turn-on Rise Time	t_r		-	36	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	nS
Turn-Off Fall Time	t_f		-	24	-	nS
Total Gate Charge	Q_g	$V_{DS}=48V, I_D=30A, V_{GS}=10V$	-	80	-	nC
Gate-Source Charge	Q_{gs}		-	25	-	nC
Gate-Drain Charge	Q_{gd}		-	22	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. EAS condition :T j=25 $^{\circ}\text{C}$, L=0.5mH, VDD=50V, VG=10V, Rg=25 Ω .
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production.

Characteristics Curves

Figure 1 Output Characteristics

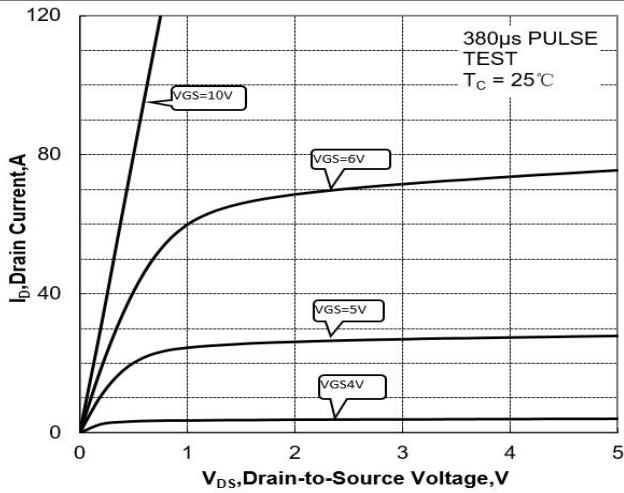


Figure 2 Transfer Characteristics

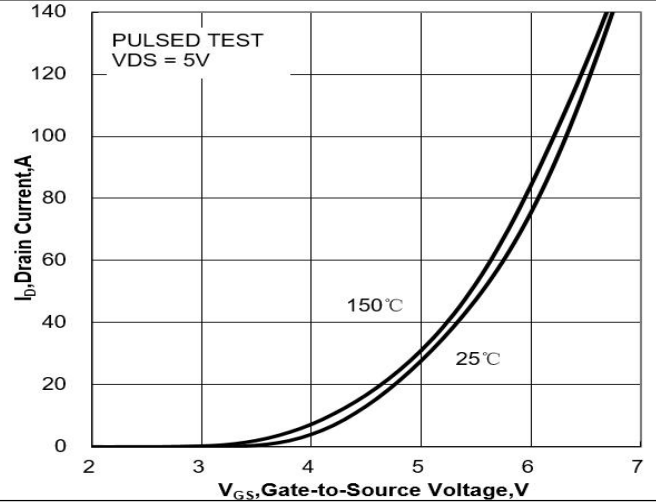


Figure 3 On-Resistance vs. ID and VGS

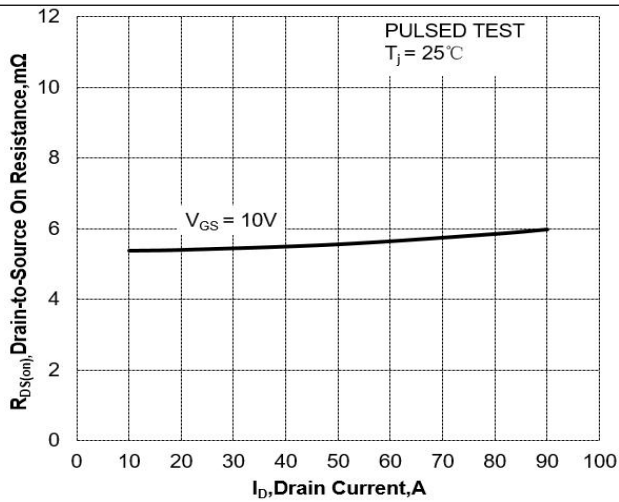


Figure 4 On-Resistance vs. Junction Temperature

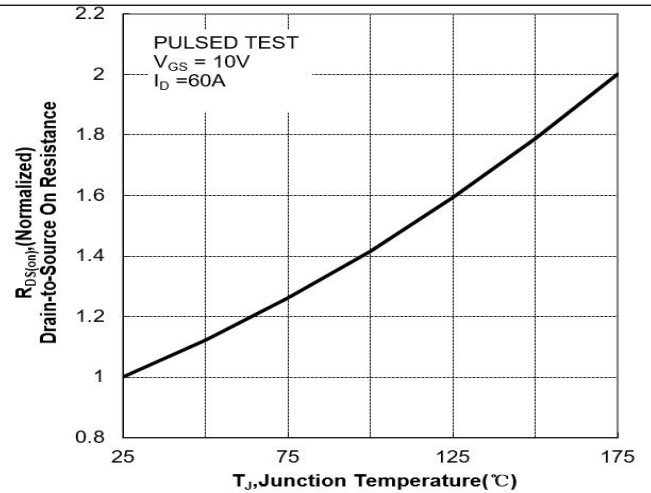


Figure 5 On-Resistance vs. VGS

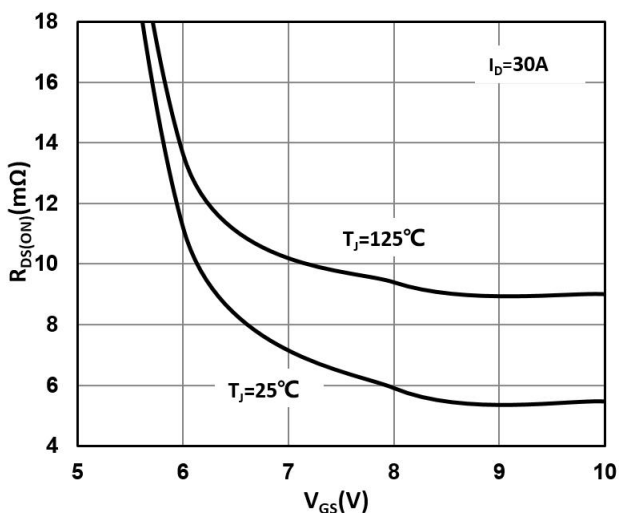


Figure 6 Body Diode Forward Voltage

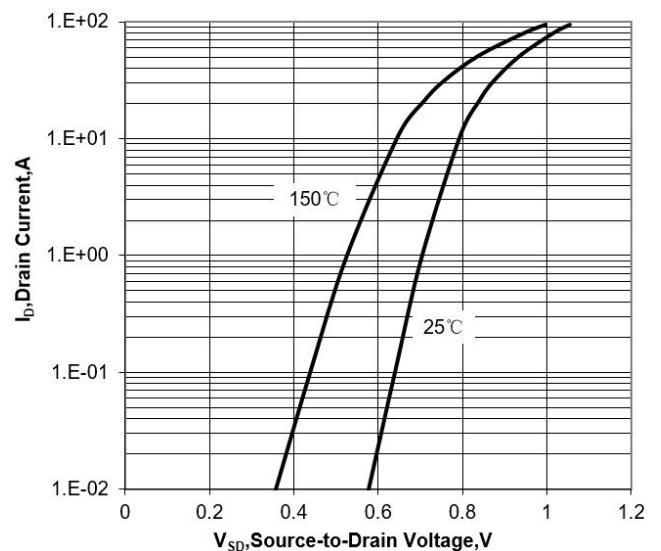


Figure 7 Gate-Charge Characteristics

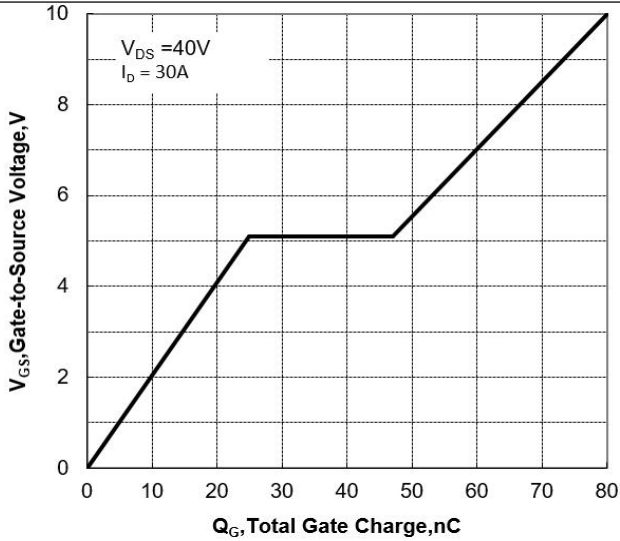


Figure 8 Capacitance Characteristics

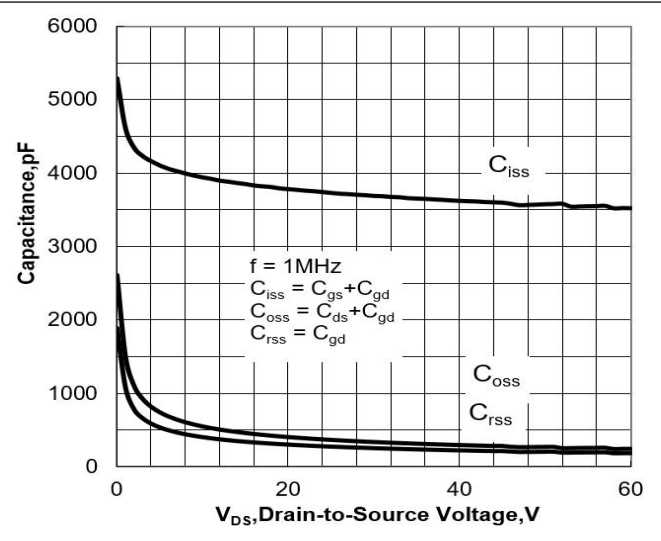


Figure 9 Maximum Forward Biased Safe Operation Area

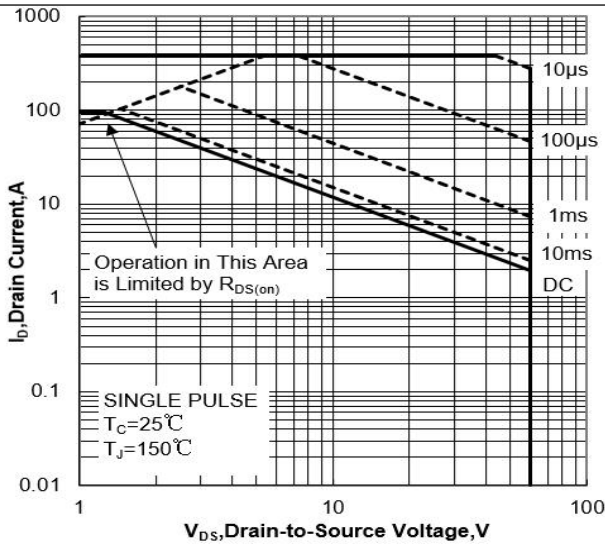


Figure 10 Single Pulse Power Rating Junction-to-Ambient

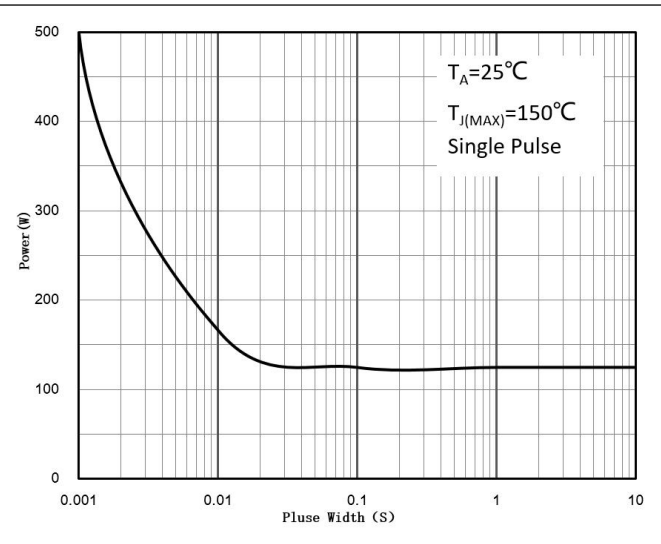
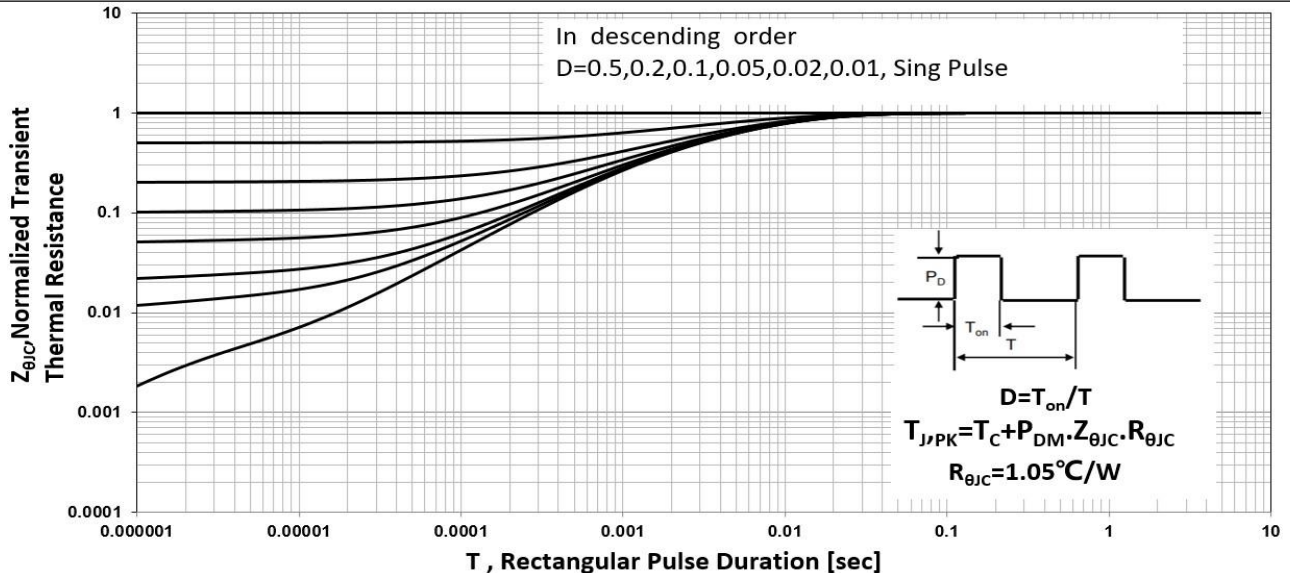
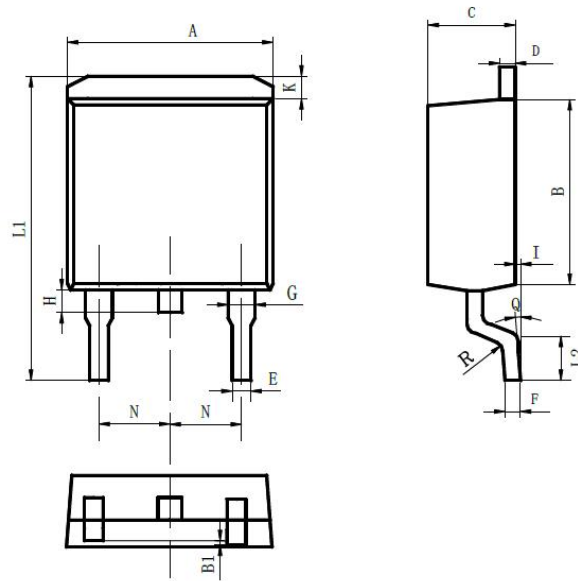


Figure 11 Normalized Maximum Transient Thermal Impedance





Items	Values(mm)	
	MIN	MAX
A	9.80	10.40
B	8.90	9.50
B1	0	0.10
C	4.40	4.80
D	1.16	1.37
E	0.70	0.95
F	0.30	0.60
G	1.07	1.47
H	1.30	1.80
K	0.95	1.37
L1	14.50	16.50
L2	1.60	2.30
I	0	0.2
Q	0°	8°
R	0.4	
N	2.39	2.69

TO-263 Package



NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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